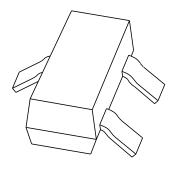
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT17Schottky barrier diode

Product specification Supersedes data of April 1992 File under Discrete Semiconductors, SC01 1996 Mar 20





Philips Semiconductors Product specification

Schottky barrier diode

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FEATURES

- Low forward voltage
- Small SMD package
- Low capacitance.

APPLICATIONS

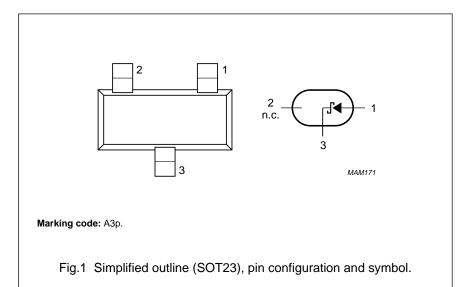
- UHF mixer
- Sampling circuits
- Modulators
- Phase detection.

PINNING

PIN	DESCRIPTION	
1	anode	
2	not connected	
3	cathode	

DESCRIPTION

Planar Schottky barrier diode in a SOT23 small plastic SMD package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		4	V
I _F	continuous forward current		30	mA
T _{stg}	storage temperature		+150	°C
T _j	junction temperature	_	100	°C

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.2		
		I _F = 0.1 mA	350	mV
		I _F = 1 mA	450	mV
		I _F = 10 mA	600	mV
I _R	reverse current	V _R = 3 V; see Fig.3	0.25	μΑ
		V _R = 3 V; T _{amb} = 60 °C; see Fig.3	1.25	μΑ
r _D	diode forward resistance	f = 1 kHz; I _F = 5 mA	15	Ω
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 0 \text{ V}$; see Fig.4	1	pF
F	noise figure	f = 900 MHz; note 1	8	dB

Note

1. The local oscillator is adjusted for a diode current of 2 mA. IF amplifier noise $F_{if} = 1.5 \text{ dB}$; f = 35 MHz.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

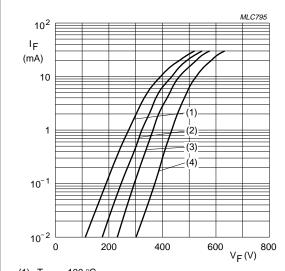
Note

1. Refer to SOT23 standard mounting conditions.

Schottky barrier diode

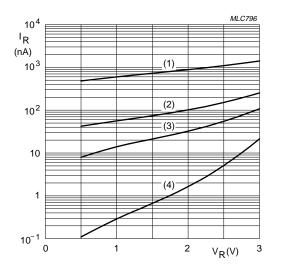
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GRAPHICAL DATA



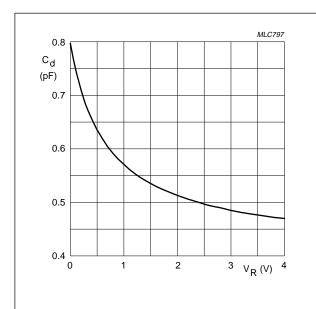
- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) $T_{amb} = 60 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.
- (4) $T_{amb} = -40 \,^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 100 \,^{\circ}C$.
- (2) $T_{amb} = 60 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.
- (4) $T_{amb} = -40 \,^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

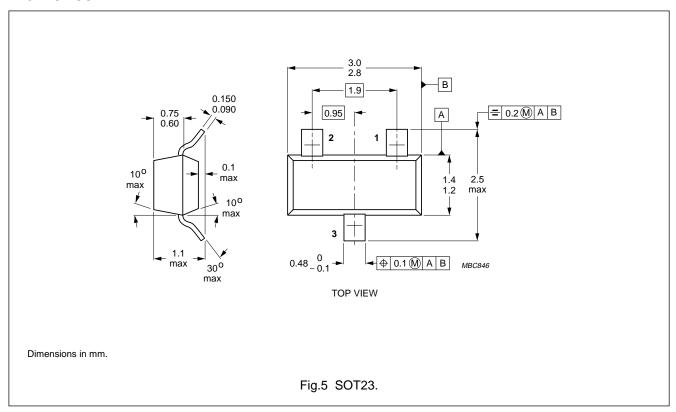
Fig.4 Diode capacitance as a function of reverse voltage; typical values.

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PACKAGE OUTLINE



DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.